

20A, 500V N-CHANNEL POWER MOSFET

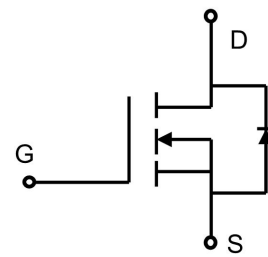
GENERAL DESCRIPTION

This power mosfet is an N-channel enhancement mode power MOS field effect transistor which is produced using Hi-semicon proprietary F-Cell™ structure VDMOS technology. The improved planar stripe cell and the improved guard ring terminal have been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode.

These devices are widely used in AC-DC power suppliers, DC-DC converters and H-bridge PWM motor drivers.

Features

- ◆ $V_{DS}=500V$, $I_D=20A$
- ◆ $R_{DS(ON)}$
TYP: $0.20\Omega @ V_{GS}=10V$
- ◆ Low gate charge
- ◆ Low C_{rss}
- ◆ Fast switching
- ◆ Improved dv/dt capability



ORDERING INFORMATION

Part No.	Package	Marking	Material	Packing
SFF20N50	TO-220F-3L	SFF20N50	Pb free	Tube

ABSOLUTE MAXIMUM RATINGS (T_J=25°C unless otherwise noted)

Characteristics	Symbol	Ratings	Unit
Drain-Source Voltage	V _{DS}	500	V
Gate-Source Voltage	V _{GS}	±30	V
Drain Current	I _D	T _C = 25°C	20
		T _C = 100°C	12.6
Drain Current Pulsed (Note 1)	I _{DM}	80	A
Power Dissipation(T _C =25°C) -Derate above 25°C	P _D	72	W
		0.58	W/°C
Single Pulsed Avalanche Energy (Note 2)	E _{AS}	1596	mJ
Operation Junction Temperature Range	T _J	-55~+150	°C
Storage Temperature Range	T _{stg}	-55~+150	°C
Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	TL	300	°C

THERMAL CHARACTERISTICS

Characteristics	Symbol	Ratings	Unit
Thermal Resistance, Junction-to-Case	R _{θJC}	1.74	°C/W
Thermal Resistance, Junction-to-Ambient	R _{θJA}	62.5	°C/W

ELECTRICAL CHARACTERISTICS

Characteristics	Symbol	Test conditions	Min.	Typ.	Max	Unit
Off Characteristics						
Drain -Source Breakdown Voltage	B _V DSS	V _{GS} =0V, I _D =250μA	500	--	--	V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =500V, V _{GS} =0V	--	--	1.0	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =30V, V _{DS} =0V	--	--	100	nA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =-30V, V _{DS} =0V	--	--	-100	nA
On Characteristics						
Gate Threshold Voltage	V _{GS(th)}	V _{GS} = V _{DS} , I _D =250μA	2.0	--	4.0	V
Static Drain- Source On State Resistance	R _{DS(on)}	V _{GS} =10V, I _D =4.0A	--	0.20	0.27	mΩ
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{DS} =25V V _{GS} =0V f=1.0MHZ	--	2687.7	--	pF
Output Capacitance	C _{oss}		--	355	--	
Reverse Transfer Capacitance	C _{rss}		--	10.3	--	
Switching Characteristics						
Turn-on Delay Time	t _{d(on)}	V _{DD} =250V, R _G =25Ω V _{GS} =10V, I _D =20A (Note2, 3)	--	27.2	--	ns
Turn-on Rise Time	t _r		--	47.5	--	
Turn-off Delay Time	t _{d(off)}		--	78.7	--	
Turn-off Fall Time	t _f		--	41.1	--	

Total Gate Charge	Q_g	$V_{DS}=400V, I_D=20A$ $V_{GS}=10V$ (Note2, 3)	--	49.5	--	nc
Gate-Source Charge	Q_{gs}		--	14.28	--	
Gate-Drain Charge	Q_{gd}		--	16.95	--	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

Characteristics	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Continuous Source Current	I_S	Integral Reverse P-N Junction Diode in the MOSFET	--	--	20.0	A
Pulsed Source Current	I_{SM}		--	--	80.0	
Diode Forward Voltage	V_{SD}	$I_S=20A, V_{GS}=0V$	--	--	1.4	V
Reverse Recovery Time	T_{rr}	$I_F=20A$ $dI_F/dt=100A/\mu S$	--	570.3	--	ns
Reverse Recovery Charge	Q_{rr}		--	7.35	--	μC

1. Pulse width limited by maximum junction temperature
2. $L=30mH, I_{AS}=9.90A, V_{DD}=50V, R_G=25\Omega$, starting $T_J=25^\circ C$
3. Pulse Test: Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$
4. Essentially independent of operating temperature

Typical Performance Characteristics

Figure 1. On-Region Characteristics

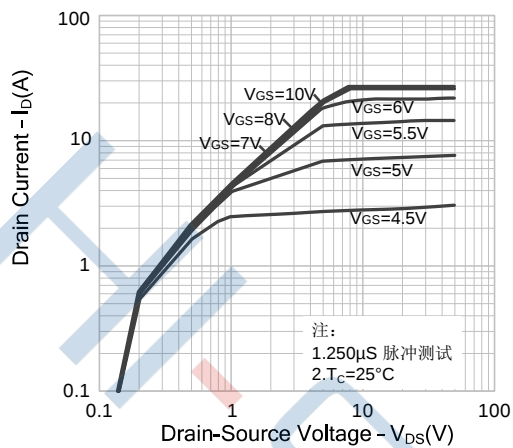


Figure 2. Transfer Characteristics

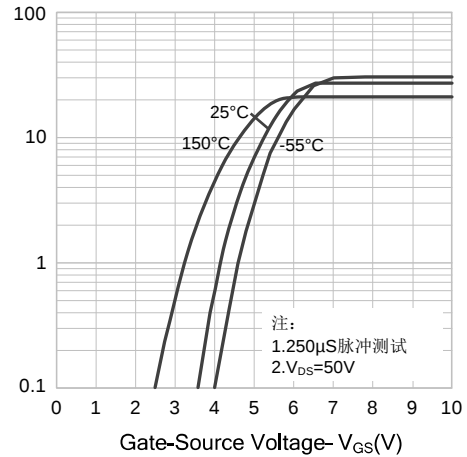


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

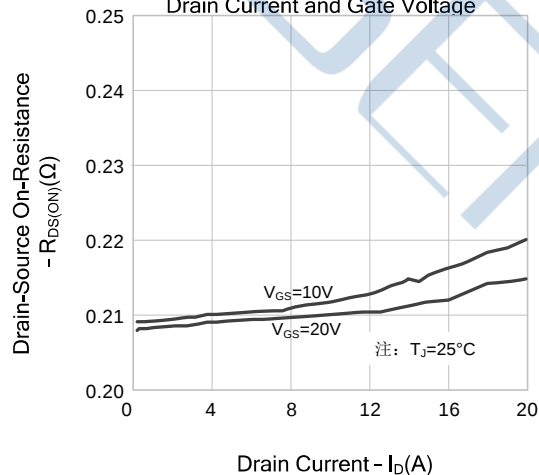


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

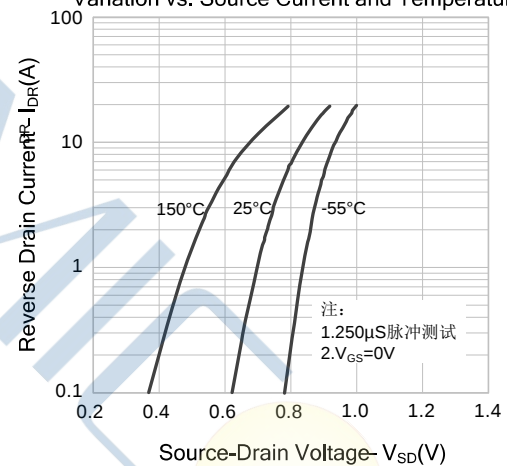


Figure 5. Capacitance Characteristics

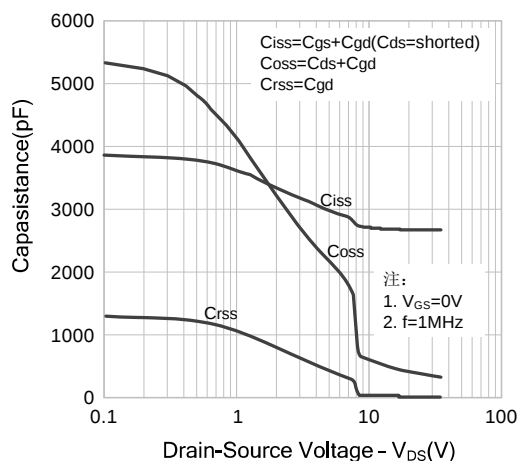
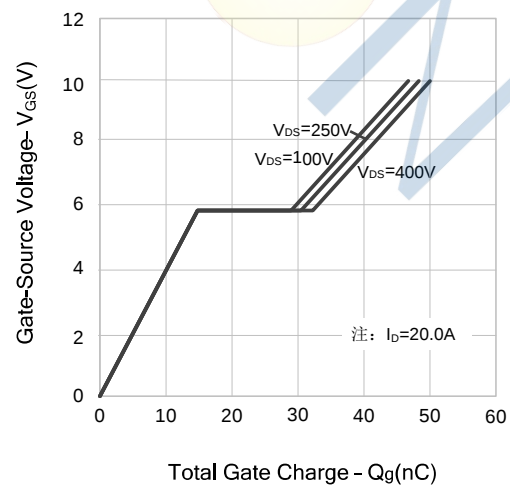


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics

Figure 7. Breakdown Voltage Variation vs. Temperature

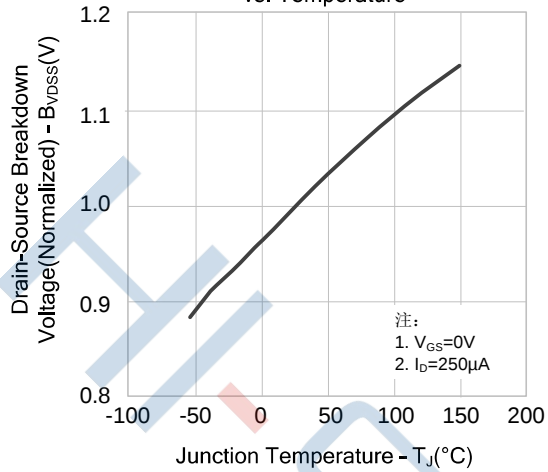


Figure 8. On-resistance Variation vs. Temperature

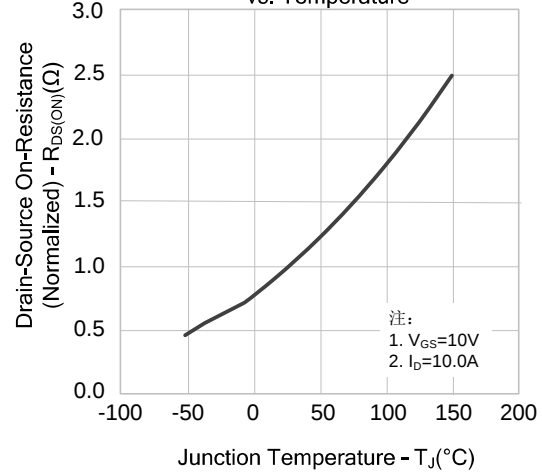


Figure 9 . Max. Safe Operating Area

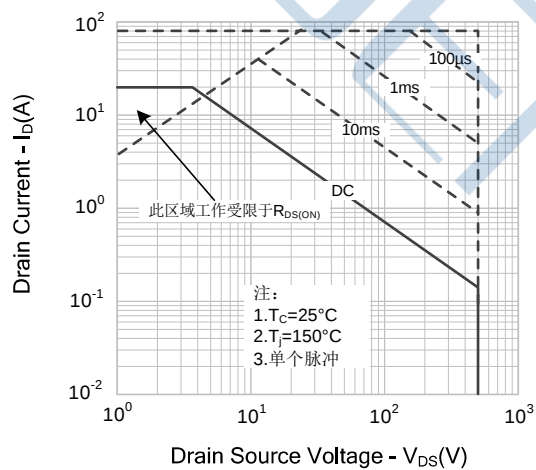
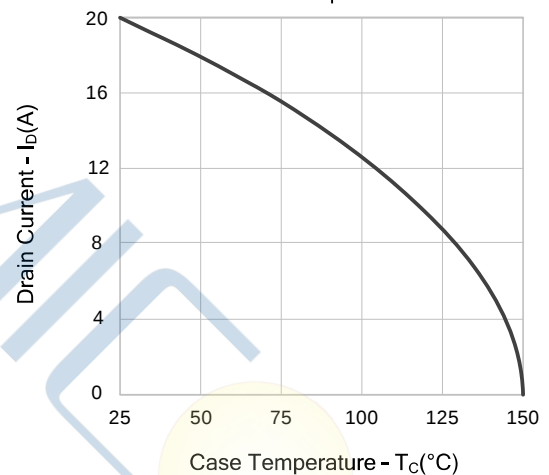
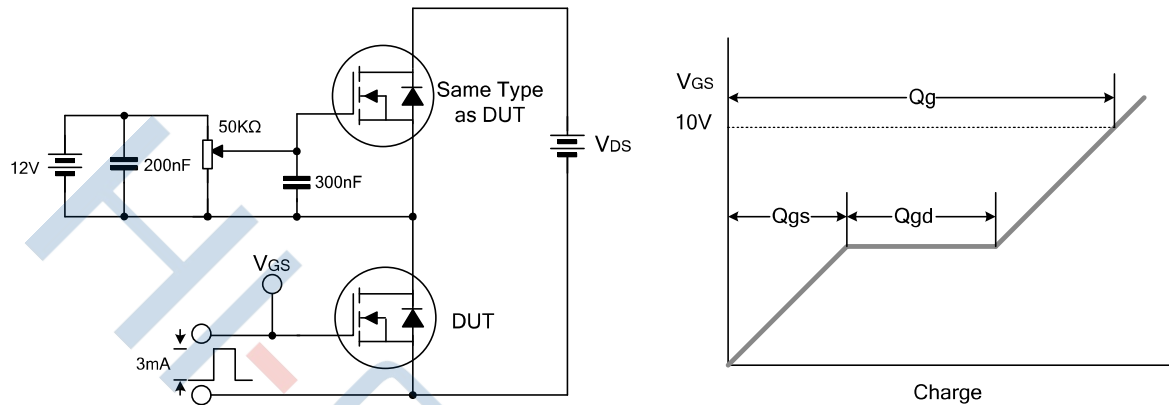


Figure 10. Maximum Drain Current vs. Case Temperature

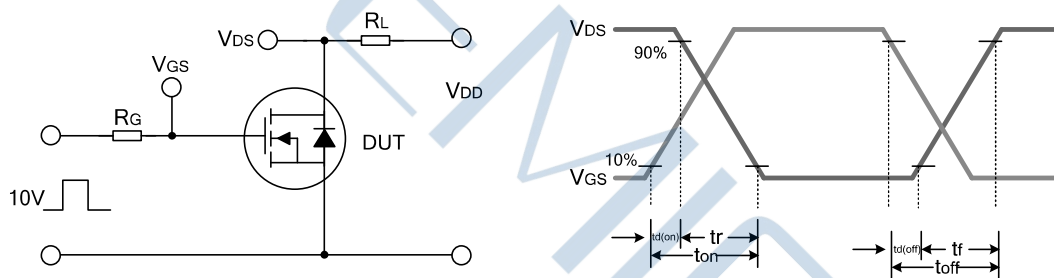


Test Circuit

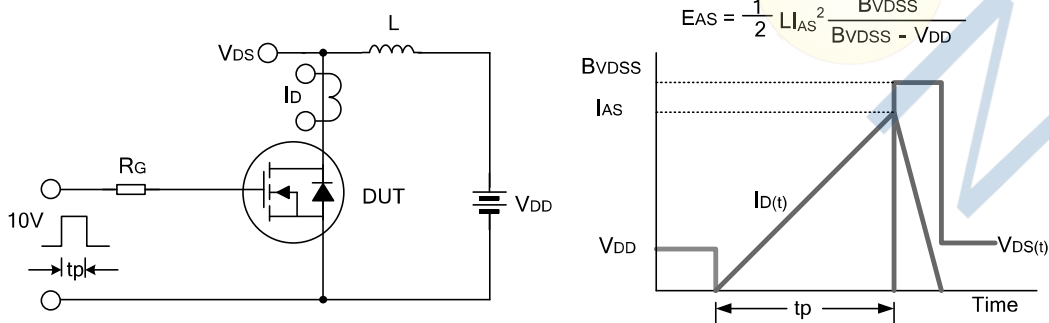
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveform

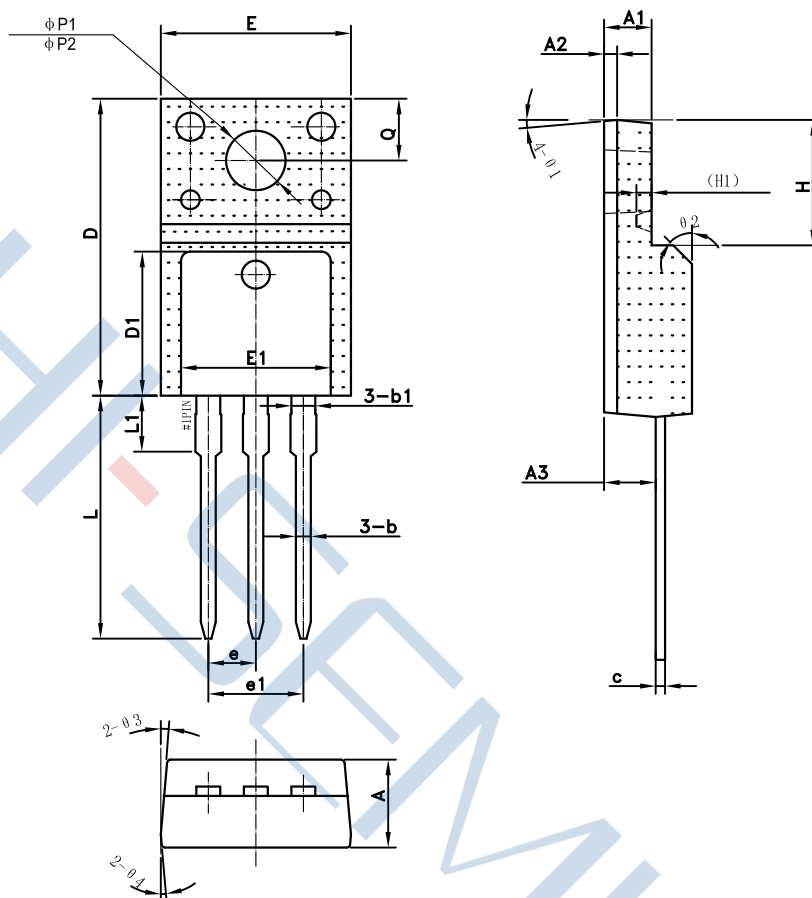


Undamped Inductive Switching Test Circuit & Waveform



Package Dimensions of TO-220F-3L

Unit:mm



Symbol	Mechanical Dimension/mm		
	Min	Typ	Max
A	4.50	4.70	4.90
A1	2.44	2.54	2.64
A2	0.60	0.70	0.80
A3	2.56	2.76	2.96
b	0.70	0.80	0.95
b1		1.28	
c	0.45	0.50	0.65
D	15.67	15.87	16.07
D1		7.70	
E	9.96	10.16	10.36
E1		8.00	
e		2.54	
e1		5.08	
H	6.50	6.70	6.90
(H1)		(0.81)	
L	12.48	12.98	13.20
L1		2.93	
$\phi P1$	2.98	3.18	3.38
$\phi P2$	3.20	3.40	3.60
Q	3.10	3.30	3.50
$\theta 1$		5°	
$\theta 2$		45°	
$\theta 3$		5°	
$\theta 4$		5°	

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